ON Semiconductor®

FDG8842CZ

Complementary PowerTrench® MOSFET

Q1:30V,0.75A,0.4Ω; Q2:–25V,–0.41A,1.1Ω

Features

Q1: N-Channel

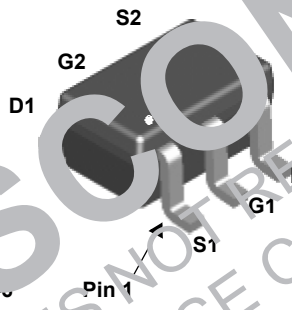
- Max $r_{DS(on)}$ = 0.4Ω at V_{GS} = 4.5V, I_D = 0.75A
- Max $r_{DS(on)}$ = 0.5Ω at V_{GS} = 2.7V, I_D = 0.67A

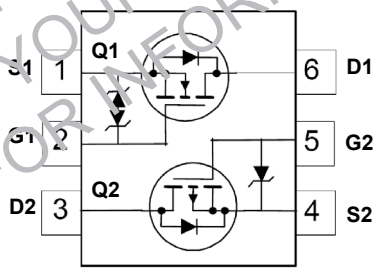
Q2: P-Channel

- Max $r_{DS(on)}$ = 1.1Ω at V_{GS} = –4.5V, I_D = –0.41A
- Max $r_{DS(on)}$ = 1.5Ω at V_{GS} = –2.7V, I_D = –0.25A
- Very low level gate drive requirements allowing direct operation in 3V circuits($V_{GS(th)}$ <1.5V)
- Very small package outline SC70-6
- RoHS Compliant

General Description

These N & P-Channel logic level enhancement mode field effect transistors are produced using ON Semiconductor's proprietary, high cell density DMOS technology. This very high density process is especially tailored to minimize on-state resistance. These devices have been designed especially for low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETs. Since bias resistors are not required, this dual digital FET can replace several different digital transistors, with different bias resistor values.





MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Q1	Q2	Units
V_{DS}	Drain to Source Voltage		30	–25	V
V_{GS}	Gate to Source Voltage		±12	–8	V
I_D	Drain Current -Continuous		0.75	–0.41	A
	-Pulsed		2.2	–1.2	
P_D	Power Dissipation for Single Operation	(Note 1a)	0.36		W
		(Note 1b)	0.30		
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150		°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Single operation	(Note 1a)	350	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Single operation	(Note 1b)	415	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.42	FDG8842CZ	7”	8mm	3000 units

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V I_D = –250μA, V_{GS} = 0V	Q1 Q2	30 –25			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C I_D = –250μA, referenced to 25°C	Q1 Q2		25 –21		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24V, V_{GS} = 0V V_{DS} = –20V, V_{GS} = 0V	Q1 Q2			1 –1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±12V, V_{DS}= 0V V_{GS} = –8V, V_{DS}= 0V	Q1 Q2			±10 –100	μA nA
On Characteristics							
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA V_{GS} = V_{DS}, I_D = –250μA	Q1 Q2	0.65 –0.65	1.0 –0.8	1.5 –1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C I_D = –250μA, referenced to 25°C	Q1 Q2		–3 1.8		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 4.5V, I_D = 0.75A V_{GS} = 2.7V, I_D = 0.67A V_{GS} = 4.5V, I_D = 0.75A, T_J = 125°C	Q		0.25 0.29 0.36	0.4 0.5 0.6	Ω
		V_{GS} = –4.5V, I_D = –0.41A V_{GS} = –2.7V, I_D = –0.25A V_{GS} = –4.5V, I_D = –0.41A, T_J = 125°C	Q2		0.87 1.20 1.32	1.1 1.5 1.9	
g_{FS}	Forward Transconductance	V_{DS} = 5V, I_D = 0.75A V_{DS} = –5V, I_D = –0.41A	Q1 Q2		3 8		S
Dynamic Characteristics							
C_{iss}	Input Capacitance	Q1 V_{DS} = 10V, V_{GS} = 0V, f= 1MHz Q2	Q1 Q2		90 70	120 100	pF
C_{oss}	Output Capacitance	V_{DS} = –10V, V_{GS} = 0V, f= 1MHz	Q1 Q2		20 30	30 40	pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		15 15	25 25	pF
Switching Characteristics (note 2)							
$t_{d(on)}$	Turn-On Delay Time	Q1 V_{DD} = 5V, I_D = 0.5A, V_{GS} = 4.5V,R_{GEN} = 6Ω Q2 V_{DD} = –5V, I_D = –0.5A, V_{GS} = –4.5V,R_{GEN} = 6Ω	Q1 Q2		4 6	10 12	ns
t_r	Rise Time		Q1 Q2		1 16	10 29	ns
$t_{d(off)}$	Turn-Off Delay Time		Q1 Q2		9 35	18 56	ns
t_f	Fall Time		Q1 Q2		1 40	10 64	ns
Q_g	Total Gate Charge	Q1 V_{GS} =4.5V, V_{DD} = 5V, I_D = 0.75A Q2 V_{GS} = –4.5V, V_{DD} = –5V, I_D = –0.41A	Q1 Q2		1.03 1.20	1.44 1.68	nC
Q_{gs}	Gate to Source Charge		Q1 Q2		0.29 0.31		nC
Q_{gd}	Gate to Drain “Miller” Charge		Q1 Q2		0.17 0.22		nC

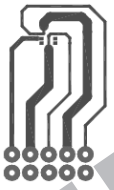
Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Drain-Source Diode Characteristics and Maximum Ratings							
I_S	Maximum Continuous Drain-Source Diode Forward Current		Q1 Q2			0.3 –0.3	A
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = 0.3A (Note 2) V_{GS} = 0V, I_S = –0.3A (Note 2)	Q1 Q2		0.76 –0.84	1.2 –1.2	V

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.

a. 350°C/W when mounted on a 1 in^2 pad of 2 oz copper .



b. 415°C/W when mounted on a minimum pad of 2 oz copper.

Scale 1:1 on letter size paper.

2. Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted

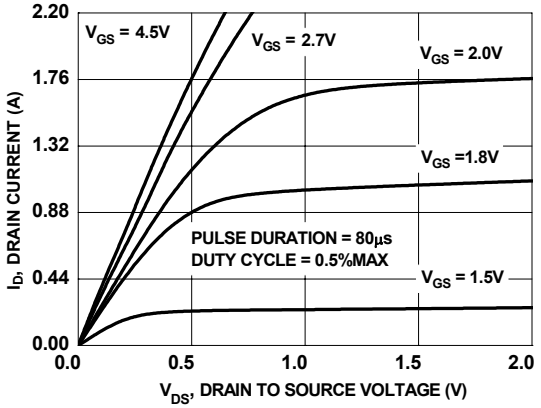


Figure 1. On-Region Characteristics

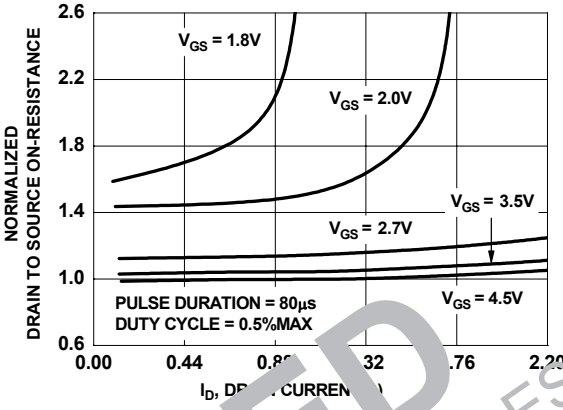


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

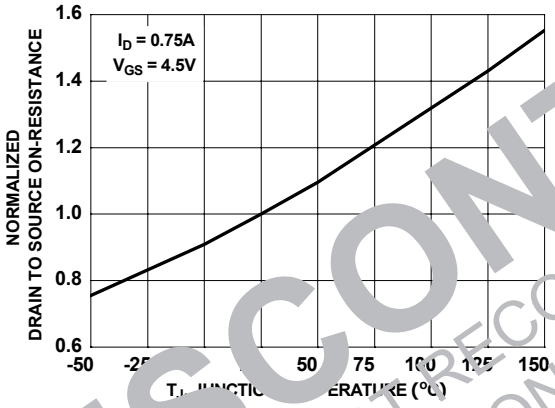


Figure 3. Normalized On-Resistance vs Junction Temperature

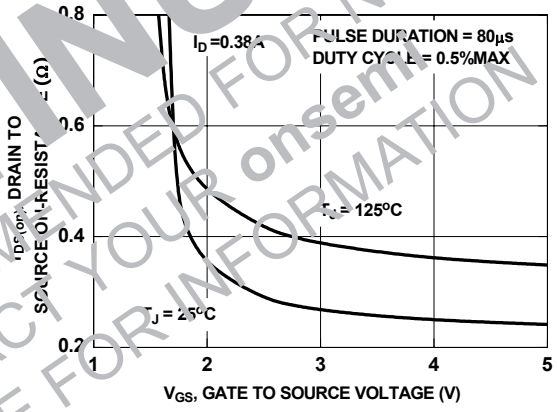


Figure 4. On-Resistance vs Gate to Source Voltage

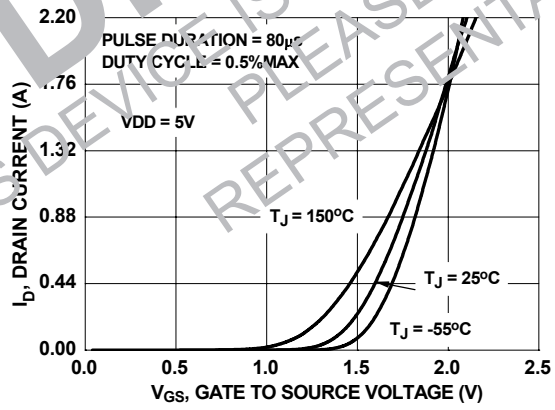


Figure 5. Transfer Characteristics

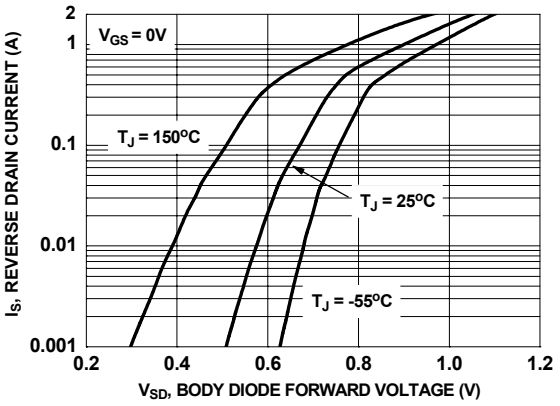


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted

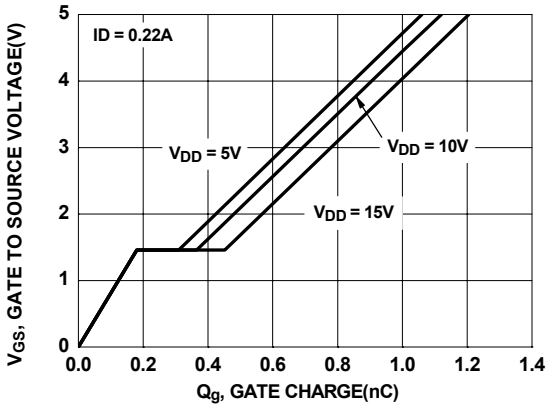


Figure 7. Gate Charge Characteristics

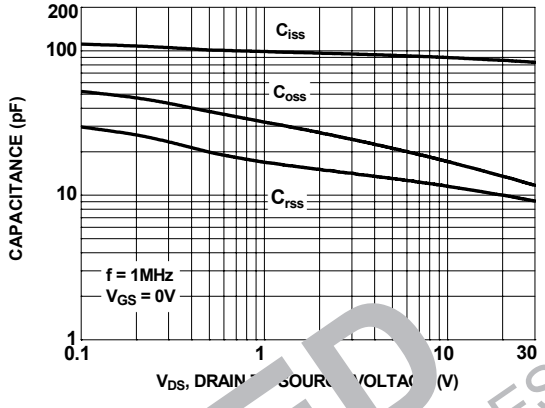


Figure 8. Capacitance vs Drain to Source Voltage

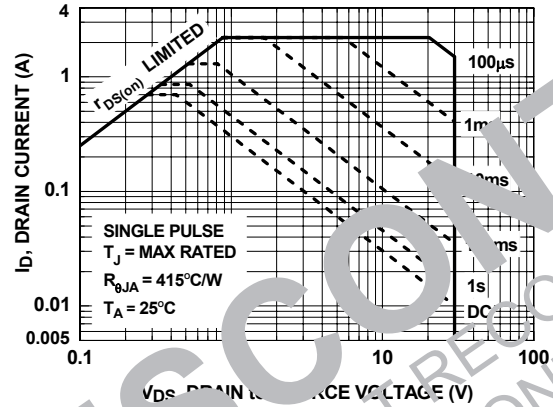


Figure 9. Forward Bias Safe Operating Area

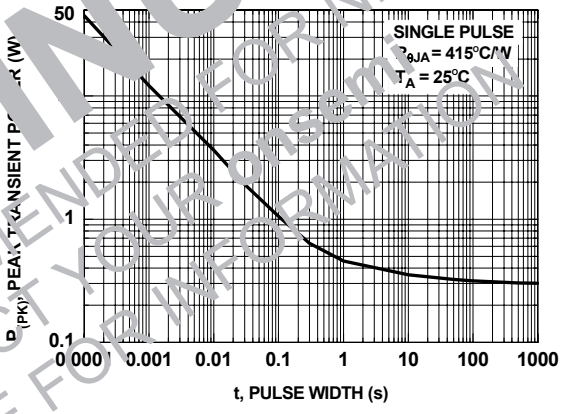


Figure 10. Single Pulse Maximum Power Dissipation

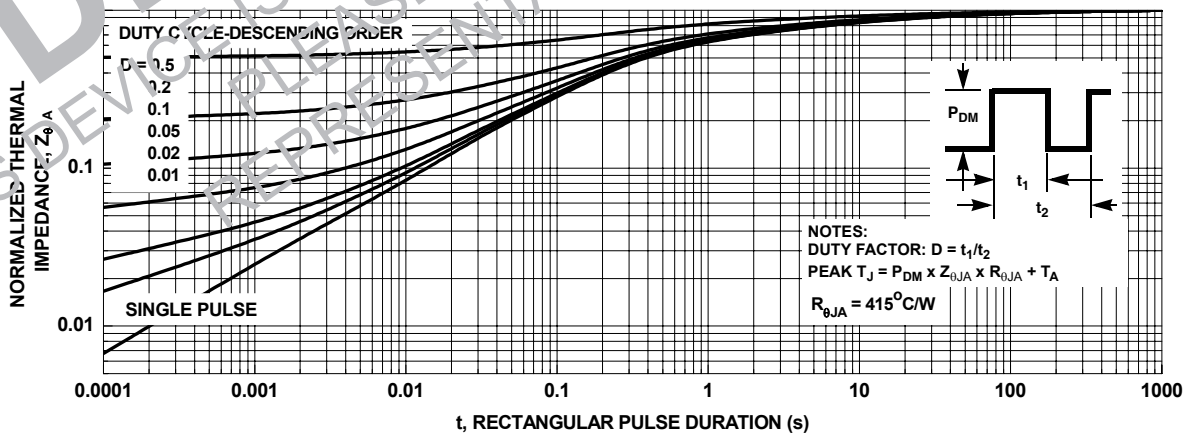


Figure 11. Transient Thermal Response Curve

Typical Characteristics (Q2 P-Channel) T_J = 25°C unless otherwise noted

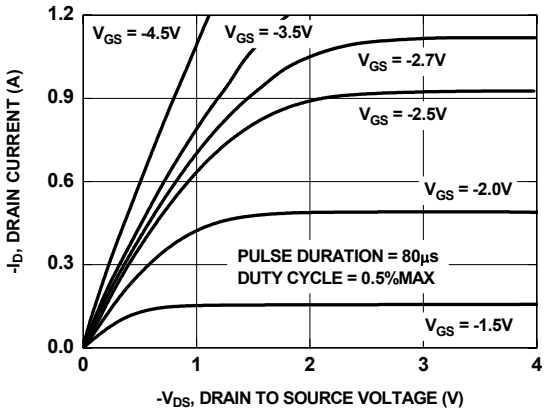


Figure 13. On Region Characteristics

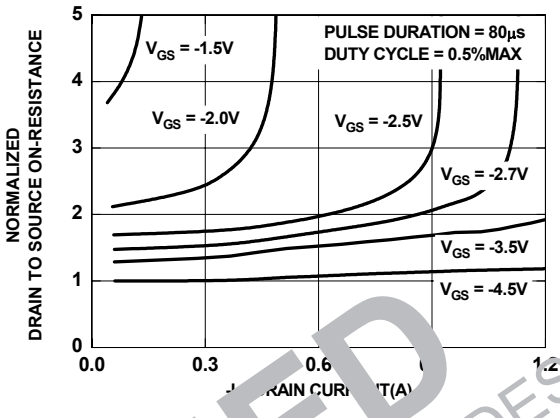


Figure 14. Normalized On-Resistance vs Drain Current and Gate Voltage

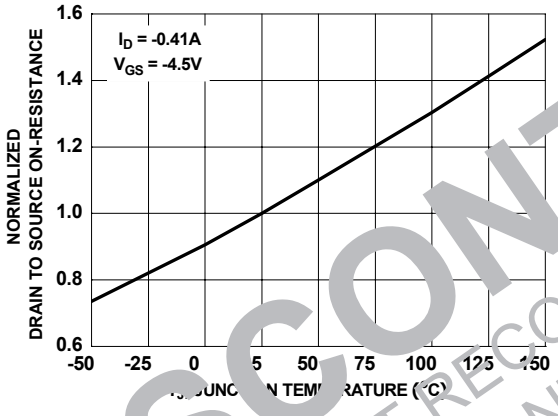


Figure 15. Normalized On Resistance vs Junction Temperature

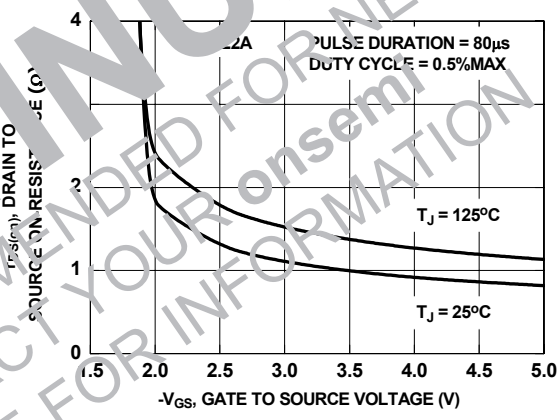


Figure 16. On-Resistance vs Gate to Source Voltage

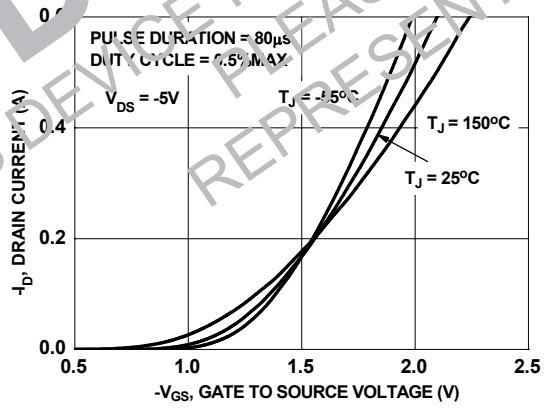


Figure 17. Transfer Characteristics

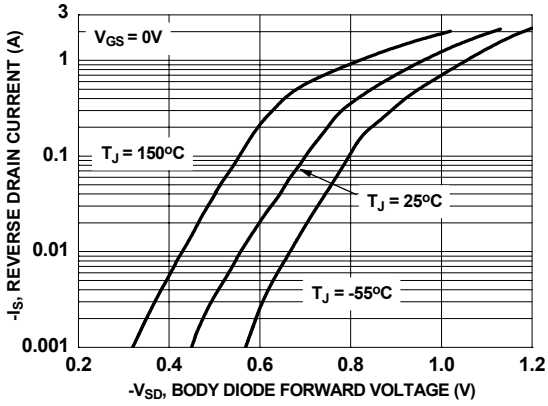


Figure 18. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics(Q2 P-Channel) T_J = 25°C unless otherwise noted

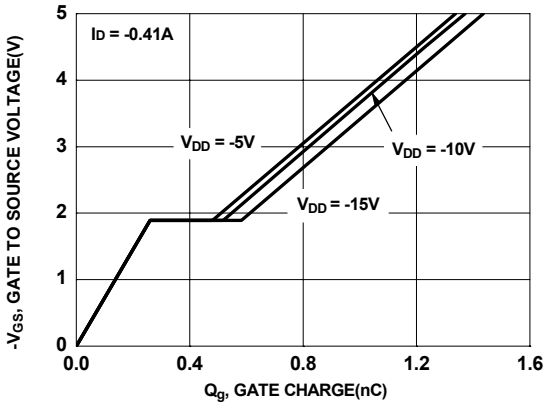


Figure 19. Gate Charge Characteristics

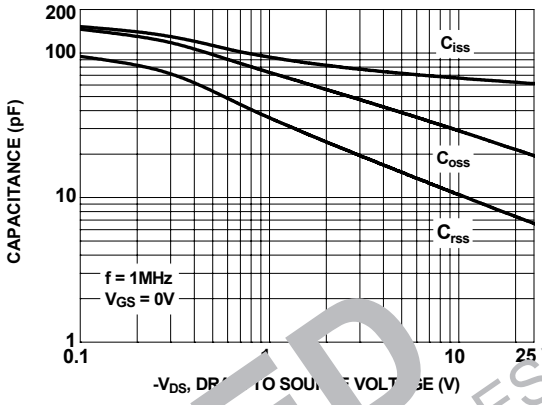


Figure 20. Capacitance vs Drain to Source Voltage

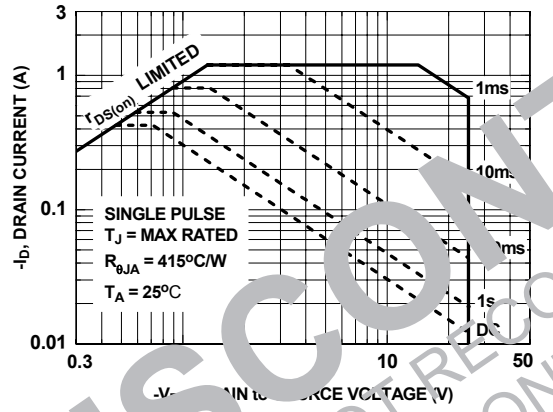


Figure 21. Forward Bias Safe Operating Area

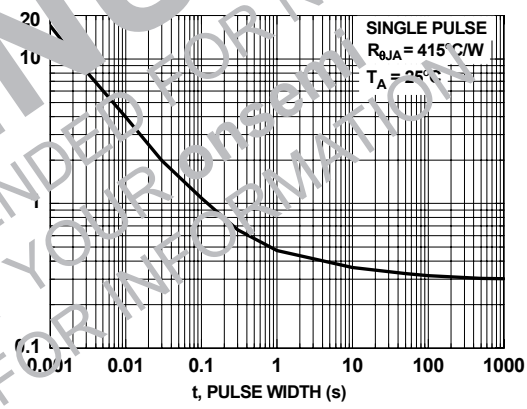


Figure 22. Single Pulse Maximum Power Dissipation

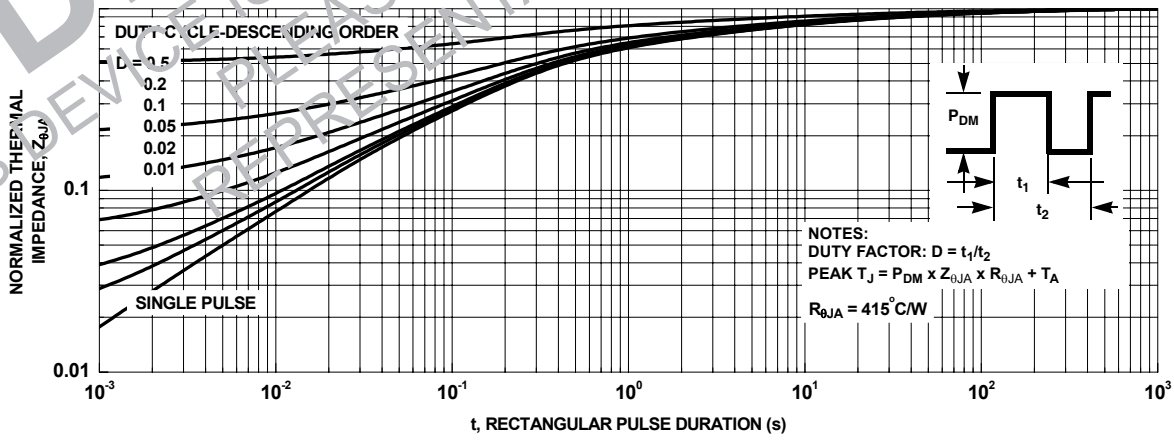


Figure 23. Transient Thermal Response Curve

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